

**2SA984,
984K**



2003A

PNP/NPN Epitaxial Planar
Silicon Transistors

**2SC2274,
2274K**

Low Frequency Power Amp Applications

©465F

Features

- . High breakdown voltage ($V_{CE0} \geq 50/80V$).
- . High current ($I_C=500mA$).
- . Low saturation voltage.

(): 2SA984,984K

Absolute Maximum Ratings at Ta=25°C		A984,C2274	A984K,C2274K	unit
Collector to Base Voltage	V_{CBO}	(-) 60	(-) 100	V
Collector to Emitter Voltage	V_{CEO}	(-) 50	(-) 80	V
Emitter to Base Voltage	V_{EBO}		(-) 5	V
Collector Current	I_C	(-) 500		mA
	i_{cp}	(-) 800		mA
Collector Dissipation	P_C		600	mW
Junction Temperature	T_j		150	°C
Storage Temperature	T_{stg}	-55 to +150		°C

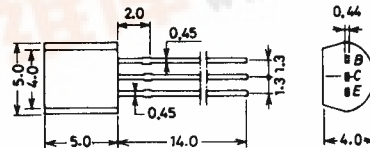
Electrical characteristics at Ta=25°C

		min	typ	max	unit
Collector Cutoff Current	I_{CBO} $V_{CB}=(-)40V, I_E=0$			(-) 1.0	uA
Emitter Cutoff Current	I_{EBO} $V_{EB}=(-)4V, I_C=0$			(-) 1.0	uA
DC Current Gain	$h_{FE}(1)$ $V_{CE}=(-)5V, I_C=(-)50mA$		60*	320*	
	$h_{FE}(2)$ $V_{CE}=(-)5V, I_C=(-)400mA$ (pulse)		35		
G-B Product	f_T $V_{CE}=(-)10V, I_C=(-)10mA$		120		MHz
	c_{ob} $V_{CB}=(-)10V, f=1MHz$		(9)		pF
C-E Saturation Voltage	$V_{CE}(sat)$ $I_C=(-)400mA,$ $I_B=(-)40mA$		(-0.25)	(-0.6)	V
			0.2	0.6	V
B-E Saturation Voltage	$V_{BE}(sat)$ " "		(-) 0.9	(-) 1.2	V
C-B Breakdown Voltage	$V(BR)_{CBO}$ $I_C=(-)10uA,$ $I_E=0$		A984,C2274 (-) 60		V
			A984K,C2274K (-) 100		V
C-E Breakdown Voltage	$V(BR)_{CEO}$ $I_C=(-)1mA,$ $R_{BE}=open$		A984,C2274 (-) 50		V
			A984K,C2274K (-) 80		V
E-B Breakdown Voltage	$V(BR)_{EBO}$ $I_E=(-)10uA, I_C=0$		(-) 5		V

* The 2SA984,K, 2SC2274,K are classified by 50mA h_{FE} as follows.

60	D	120	100	E	200	160	F	320
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Case Outline 2003A (unit:mm)



JEDEC: TO-92
EIAJ: SC-43
SANYO: NP

B: Base
C: Collector
E: Emitter

For details, refer to the description of the 2SC2274, 2274K.